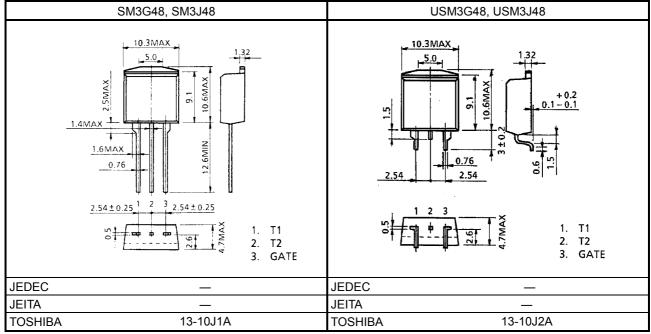
TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM3G48,USM3G48,SM3J48,USM3J48

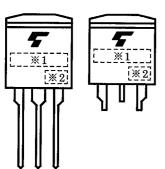
### AC POWER CONTROL APPLICATIONS

Unit in mm



Weight: 1.7g

#### **MARKING**



	NUMBER		SYMBOL	MARK		
	*1	TYPE	SM3G48, USM3G48	M3G48		
			SM3J48, USM3J48	M3J48		
	*2	L	Month (Starting from Alphabet A) Year (Last Decimal Digit of the Year of Manufacture)	Example 8A: January 1998 8B: Febrary 1998 8L: December 1998		



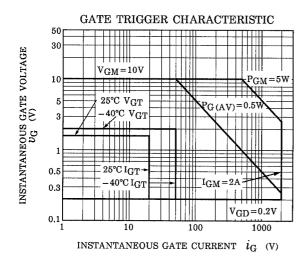
## **MAXIMUM RATINGS**

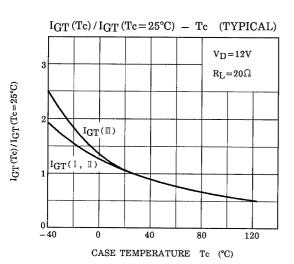
CHARACTERIS	STIC	SYMBOL	RATING	UNIT		
Repetitive Peak	(U)SM3G48	$V_{DRM}$	400	V		
Off-State Voltage	(U)SM3J48	<b>V</b> DRM	600			
R.M.S On-State Current		I <sub>T (RMS)</sub>	3	Α		
Peak One Cycle Surge (	On-State	l <del>-</del>	30 (50Hz)	А		
Current (Non-Repetitive)		ITSM	33 (60Hz)	1 ^		
I <sup>2</sup> t Limit Value		ı²t	4.5	A <sup>2</sup> s		
Critical Rate of Rise of C Current	n-State (Note 1)	di / dt	50	A / μs		
Peak Gate Power Dissip	P <sub>GM</sub>	5	W			
Average Gate Power Dis	sipation	P <sub>G</sub> (AV)	0.5	W		
Peak Forward Gate Volta	age	$V_{GM}$	10	V		
Peak Forward Gate Curr	I <sub>GM</sub>	2	Α			
Junction Temperature	_	Tj	-40~125	°C		
Storage Temperature Ra	T <sub>stg</sub>	-40~125	°C			

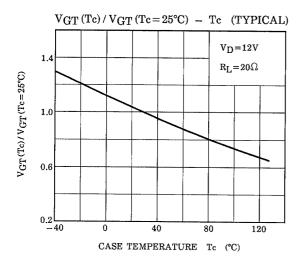
Note 1 :  $V_{DRM}$ =0.5×Rated  $I_{TM}$ ≤4.5A  $t_{gw}$ ≥10 $\mu$ s  $t_{gr}$ ≤250ns  $i_{gp}$ = $I_{GT}$ ×2.0

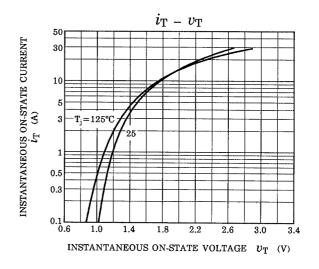
## **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

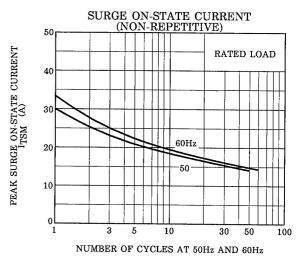
CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT	
Repetitive Peak Off-State Current	I <sub>DRM</sub>	V <sub>DRM</sub> =Rated		_	_	20	μА	
	1	V <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =20Ω	T2 (+), Gate (+)	_	_	1.5	V
Cata Trigger Voltage	Ш			T2 (+), Gate (-)	_	_	1.5	
Gate Trigger Voltage	III			T2 (-), Gate (-)	_	_	1.5	
	IV			T2 (-), Gate (+)	_	_	_	
	1	I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =20Ω	T2 (+), Gate (+)	_	_	20	- mA
Cata Trigger Current	Ш			T2 (+), Gate (-)	_	_	20	
Gate Trigger Current	III			T2 (-), Gate (-)	_	_	20	
	IV			T2 (-), Gate (+)	_	_	_	
Peak On-State Voltage	V <sub>TM</sub>	I <sub>TM</sub> =4.5A		_	_	1.5	V	
Gate Non-Trigger Voltage	$V_{GD}$	V <sub>D</sub> =Rated, Tc=125°C		0.2	_	_	V	
Holding Current	I <sub>H</sub>	V <sub>D</sub> =12V, I <sub>TM</sub> =1A		_	_	30	mA	
Thermal Resistance	R <sub>th (j-c)</sub>	Junction to Case, AC		_	_	3.6	°C/W	
Critical Rate of Rise of Off-State Voltage	dv / dt	V <sub>DRM</sub> =Rated, T <sub>j</sub> =125°C Exponential Rise		-	300	_	V / μs	
Critical Rate of Rise of Off-State Voltage at Commutation	(dv / dt) c	V <sub>DRM</sub> =400V, T <sub>j</sub> =125°C (di /dt) c=–2.0A / ms		10	_	_	V / μs	

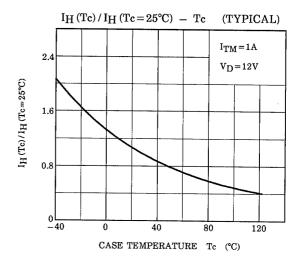


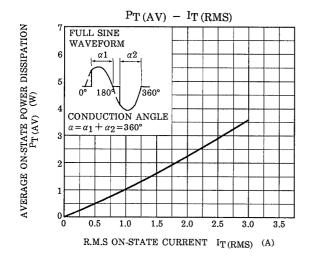


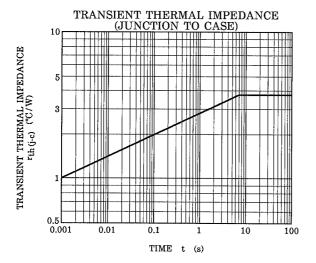


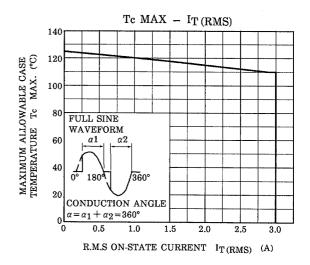


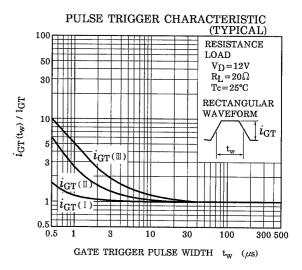












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